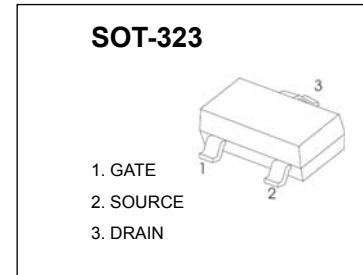


SOT-323 Plastic-Encapsulate MOSFETS

P-Channel 20-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	200 mΩ@-4.5V	2.0 A
	290 mΩ@-2.5V	



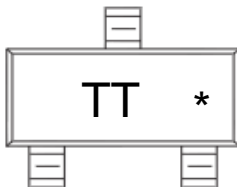
FEATURE

TrenchFET Power MOSFET

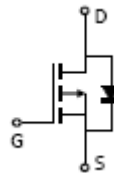
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ($T_J=150^\circ\text{C}$)	I_D	-2.0	A
Pulsed Drain Current	I_{DM}	-5	
Continuous Source-Drain Diode Current	I_S	-0.72	
Maximum Power Dissipation	P_D	0.29	W
Thermal Resistance from Junction to Ambient($t \leq 5s$)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.45		-1	
Gate-source leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1.0A$		0.012	0.160	Ω
		$V_{GS} = -2.5V, I_D = -0.5A$		0.140	0.230	
Forward transconductance ^a	g_{fs}	$V_{DS} = -5V, I_D = -1.4A$		4.0		S
Dynamic^b						
Input capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		405		pF
Output capacitance	C_{oss}			75		
Reverse transfer capacitance	C_{rss}			55		
Total gate charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -3A$		5.5	10	nC
				3.3	6	
Gate-source charge	Q_{gs}	$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -3A$		0.7		
Gate-drain charge	Q_{gd}			1.3		
Gate resistance	R_g	$f = 1MHz$		6.0		Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10V,$ $R_L = 10\Omega, I_D = -1A,$ $V_{GEN} = -4.5V, R_g = 1\Omega$		11	20	ns
Rise time	t_r			35	60	
Turn-off delay time	$t_{d(off)}$			30	50	
Fall time	t_f			10	20	
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^\circ C$			-1.3	A
Pulse diode forward current ^a	I_{SM}				-10	
Body diode voltage	V_{SD}	$I_S = -0.7A$		-0.8	-1.2	V

Notes :

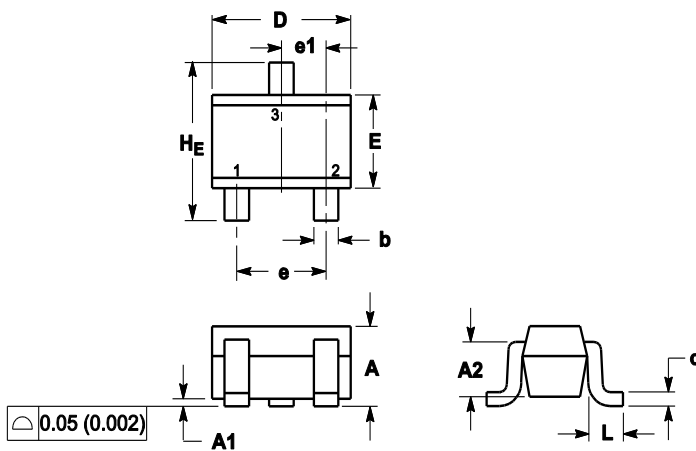
a. Pulse Test : Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

7.OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70REF			0.028REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65REF			0.026REF		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

8.SOLDERING FOOTPRINT

